

Search Hist. (7pp.) ~~1/18/05~~ (03/18/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2631	((257/52) or (257/57) or (257/66) or (257/72)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/18 17:02
L2	237	I1 and contact adj resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 17:03
S1	3	"749273".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 09:07
S2	167	((257/624) or (257/625)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/17 09:19
S3	1402	((257/327) or (257/382) or (257/383) or (257/384)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/18 17:02
S4	315	S3 and contact adj resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 17:03
S5	7	(US-20050040472-\$).did. or (US-6515340-\$ or US-6515348-\$ or US-6087706-\$ or US-6040589-\$ or US-5191397-\$ or US-5113234-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/03/17 12:16
S6	742	(thin adj film adj transistor tft).ti, ab,clm. and (active adj (layer film) semiconductor adj thin adj film) near5 (thick thickness)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:17
S7	0	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near5 (thick thickness) near5 ".ANG.")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:18
S8	0	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 ".ANG.")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:18

S9	63	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 (".ANG." ".mu.m" Angstrom))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:29
S10	33	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 (".ANG." ".mu.m" Angstrom)) and (thick thickness).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:31
S11	4	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 (".ANG." ".mu.m" Angstrom)) and (thick thickness) near4 active.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:15
S12	6	"665204".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:17
S13	1	InP near4 buffer and buffer near4 graded and graded near4 InGaAsP	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:18
S14	3	InP near8 buffer and buffer near8 graded and graded near8 InGaAsP	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:19
S15	5	InP near16 buffer and buffer near16 graded and graded near16 InGaAsP and (photodiode photodetect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:20
S16	8	(US-20050040472-\$).did. or (US-5113234-\$ or US-5191397-\$ or US-6040589-\$ or US-6087706-\$ or US-6515340-\$ or US-6515348-\$).did. or (EP-235827-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 15:00

S17	148	(SiGe silicon adj germanium SiC silicon adj carbide) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft) .	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 16:00
S18	67	(SiGe silicon adj germanium and SiC silicon adj carbide) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 09:12
S19	5	((SiGe silicon adj germanium) and (SiC silicon adj carbide)) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 15:15
S20	0	wo-0282526\$-.did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 15:15
S21	0	wo-0282526\$-.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 15:15
S22	1	wo-200282526\$-.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 15:17
S23	2	jp-2003046068\$-.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 15:17
S24	43	(ONO silicon adj oxynitride) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 16:05
S25	9	(US-20020014625-\$ or US-20050040472-\$).did. or (US-5113234-\$ or US-5191397-\$ or US-6040589-\$ or US-6087706-\$ or US-6515340-\$ or US-6515348-\$).did. or (EP-235827-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 09:01
S26	1	S25 and (buried adj oxide BOx)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 09:02

S27	11	(buried adj oxide BOx) near6 insulating adj (layer film) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 09:17
S28	519	(buried adj oxide SIMOx) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 09:17
S29	179	(buried adj oxide SIMOx) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft).ti, ab,clm.	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 09:19
S30	66	(buried adj oxide SIMOx) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft).ti, ab,clm. and buried	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 10:31
S31	0	(buried adj oxide SIMOx) near3 (preferabl\$1 advantage) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft).ti, ab,clm. and buried	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 10:32
S32	266	(buried adj oxide SIMOx) near12 (preferabl\$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:32
S33	10	(buried adj oxide SIMOx) near12 (preferabl\$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:42
S34	1	(buried adj oxide SIMOx) near12 (preferabl\$1 advantage) near12 wafer adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:47
S35	2	("6335231").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 10:45
S36	0	(buried adj oxide) near12 (preferabl\$1 advantage) near12 wafer adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48

S37	183	(buried adj oxide) near12 (preferabl\$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S38	104	(buried adj oxide) near6 (preferabl\$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S39	75	(buried adj oxide) near4 (preferabl\$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S40	58	(buried adj oxide) near3 (preferabl\$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S41	0	(buried adj oxide) near3 (preferabl\$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S42	2	(buried adj oxide) near6 (preferabl\$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:49
S43	5	(buried adj oxide) near8 (preferabl\$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:51
S44	2283	pixel adj electrode near6 (contact\$3 connect\$3 abut\$4) near6 (insulating buried oxide dioxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:52

S45	2045	pixel adj electrode near6 (contact\$3 connect\$3 abut\$4) near6 (insulating buried adj oxide dioxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:52
S46	785	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating buried adj oxide dioxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:53
S47	669	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating buried adj oxide dioxide) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:54
S48	415	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating buried adj oxide dioxide) and thin adj film adj transistor.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:54
S49	0	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (buried adj oxide) and thin adj film adj transistor.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:54
S50	467	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating adj (film layer)) and thin adj film adj transistor.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:55
S51	9	(US-20020014625-\$ or US-20050040472-\$).did. or (US-5113234-\$ or US-5191397-\$ or US-6040589-\$ or US-6087706-\$ or US-6515340-\$ or US-6515348-\$).did. or (EP-235827-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 11:33
S52	1	S51 and furuta.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 11:33

S53	1	S51 and furuta.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 14:20
S54	122	silicon adj oxynitride near3 dielectric adj constant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 14:20
S55	68	silicon adj oxynitride near2 dielectric adj constant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 15:39
S56	3	("6040589"):PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 15:39
S57	1	S56 and interconnect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 15:39